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MPSH30

Silicon NPN Transistor

VHF Oscillator, Mixer, IF Amp

TO-92 Type Package

Absolute Maximum Ratings:

Collector-Emitter Voltage, V_{CEO}	20V
Collector-Base Voltage, V_{CBO}	20V
Emitter-Base Voltage, V_{EBO}	3V
Collector Current, I_C	50mA
Total Power Dissipation ($T_A = +25^\circ\text{C}$), P_T	350mW
Derate above $+25^\circ\text{C}$	2.8mW/ $^\circ\text{C}$
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_T	1W
Derate above $+25^\circ\text{C}$	8mW/ $^\circ\text{C}$
Operating Junction Temperature Range, T_J	-55° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient, R_{thJA}	$+357^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case, R_{thJC}	$+125^\circ\text{C/W}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	20	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	20	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	3	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 10\text{V}, I_E = 0$	-	-	50	nA
ON Characteristics						
DC Current Gain	h_{FE}	$I_C = 4\text{mA}, V_{CE} = 5\text{V}$	20	-	200	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 5\text{mA}$	0.1	-	3.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 5\text{mA}$	-	-	0.96	V
Small-Signal Characteristics						
Current Gain-Bandwidth Product	f_T	$I_C = 4\text{mA}, V_{CE} = 10\text{V}, f = 100\text{MHz}$	300	-	800	MHz
Collector-Base Capacitance	C_{cb}	$I_E = 0, V_{CB} = 10\text{V}, f = 1\text{MHz}$	-	-	0.65	pF
Noise Figure	NF	$V_{AGC} = 2.75\text{V}, R_S = 50\Omega, f = 45\text{MHz}$	-	-	6	dB
Functional Tests						
Power Gain	G_{pe}	$V_{AGC} = 2.75\text{V}, R_S = 50\Omega, f = 45\text{MHz}$	22.5	-	31.0	dB
Forward AGC Voltage	V_{AGC}	Gain Reduction = 30dB, $R_S = 50\Omega, f = 45\text{MHz}$	4.4	-	5.4	V

